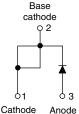


Vishay Semiconductors

Ultrafast Rectifier, 15 A FRED Pt®





Т

| | 01 | 0.3 |
|----------|---------|-------|
| ГО-220AC | Cathode | Anode |
| | | |

| PRODUCT SUMMARY | | | | | |
|----------------------------------|--------------------|--|--|--|--|
| Package | TO-220AC | | | | |
| I _{F(AV)} | 15 A | | | | |
| V_{R} | 200 V | | | | |
| V _F at I _F | 0.85 V | | | | |
| t _{rr} typ. | See Recovery table | | | | |
| T _J max. | 175 °C | | | | |
| Diode variation | Single die | | | | |

FEATURES

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- · Designed and qualified according to JEDĔC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



DESCRIPTION / APPLICATIONS

VS-MUR1520PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | |
|---|-----------------------------------|---|-------------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS | | | | |
| Peak repetitive reverse voltage | V _{RRM} | | 200 | V | | | | |
| Average rectified forward current | I _{F(AV)} | Total device, rated V _R , T _C = 150 °C | 15 | | | | | |
| Non-repetitive peak surge current | I _{FSM} | | 200 | Α | | | | |
| Peak repetitive forward current | I _{FM} | Rated V _R , square wave, 20 kHz, T _C = 150 °C | 30 | | | | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to +175 | °C | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-------------------------------------|--|-------------------------------|-----|------|----|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | TEST CONDITIONS MIN. TYP. MAX | | | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | Ι _R = 100 μΑ | 200 | - | - | | |
| Forward voltage V _F | W | I _F = 15 A | - | - | 1.05 | V | |
| | VF | I _F = 15 A, T _J = 150 °C | - | - | 0.85 | | |
| B | | $V_R = V_R$ rated | - | - | 10 | | |
| Reverse leakage current I _R | | T _J = 150 °C, V _R = V _R rated | - | - | 500 | μΑ | |
| Junction capacitance | C _T | V _R = 200 V | - | 55 | - | pF | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH | |



VS-MUR1520PbF, VS-MUR1520-N3

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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|---|------------------|-----------------------------|--|------|------|-------|-----|--|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | | |
| | | $I_F = 1.0 A$, $dI_F/dt =$ | 50 A/μs, V _R = 30 V | - | - | 35 | | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | $I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$ | - | 22 | - | ns | |
| | | T _J = 125 °C | | - | 39 | - | | |
| Peak recovery current | I _{RRM} | T _J = 25 °C | | - | 1.6 | - | ^ | |
| | | T _J = 125 °C | | - | 4.1 | - | Α | |
| Reverse recovery charge | 0 | T _J = 25 °C | | - | 19 | - | nC | |
| | Q _{rr} | T _J = 125 °C | | - | 90 | - | IIC | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|--|-----------------------------------|--|--------------|------|------------|------------------------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 1.5 | | |
| Thermal resistance, junction to ambient | R _{thJA} | | - | - | 50 | °C/W | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | | |
| Weight | | | - | 2.0 | - | g | |
| vveigni | | | - | 0.07 | - | OZ. | |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) | |
| Marking device | | Case style TO-220AC | MUR1520 | | | | |

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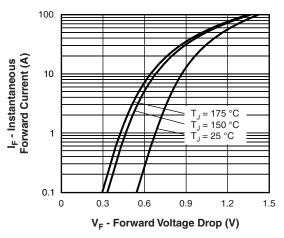


Fig. 1 - Typical Forward Voltage Drop Characteristics

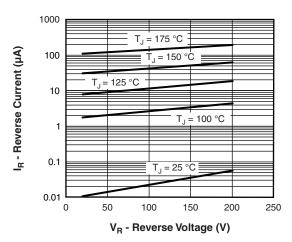


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

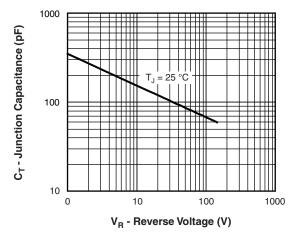


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

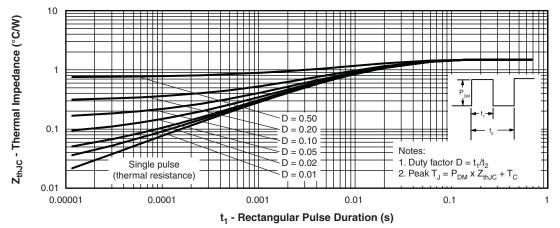


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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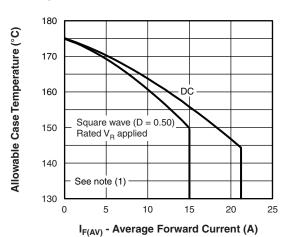


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

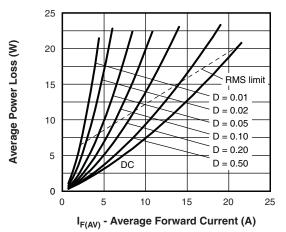


Fig. 6 - Forward Power Loss Characteristics

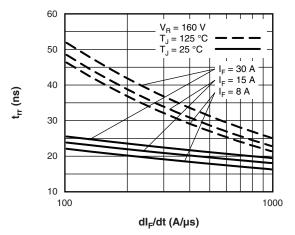


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

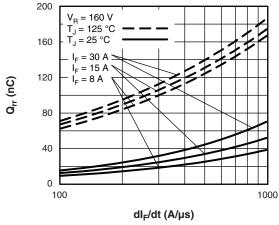


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$

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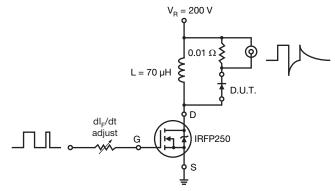
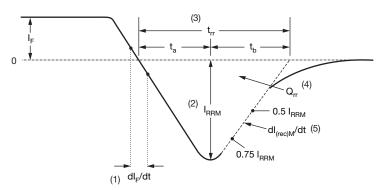


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

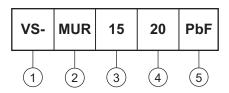


VS-MUR1520PbF, VS-MUR1520-N3

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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Ultrafast MUR series

3 - Current rating (15 = 15 A)

Voltage rating (20 = 200 V)

5 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | | | |
|---|----|------|-------------------------|--|--|--|--|--|
| PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | | | | |
| VS-MUR1520PbF | 50 | 1000 | Antistatic plastic tube | | | | | |
| VS-MUR1520-N3 | 50 | 1000 | Antistatic plastic tube | | | | | |

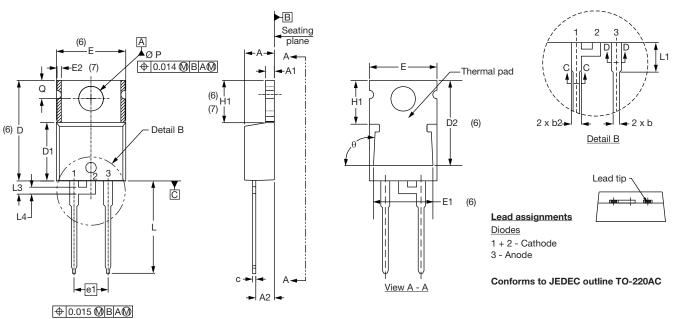
| LINKS TO RELATED DOCUMENTS | | | | | | |
|--|-------------|--------------------------|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?95221</u> | | | | | | |
| Dout moulting information | TO-220ACPbF | www.vishay.com/doc?95224 | | | | |
| Part marking information | TO-220AC-N3 | www.vishay.com/doc?95068 | | | | |
| SPICE model | | www.vishay.com/doc?95271 | | | | |



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TO-220AC

DIMENSIONS in millimeters and inches



| SYMBOL MILLIMETE | | IETERS | INC | HES | NOTES |
|------------------|-------|--------|-------|-------|-------|
| STIVIBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.25 | 4.65 | 0.167 | 0.183 | |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | |
| A2 | 2.56 | 2.92 | 0.101 | 0.115 | |
| b | 0.69 | 1.01 | 0.027 | 0.040 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 |
| D | 14.85 | 15.25 | 0.585 | 0.600 | 3 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | |
| D2 | 11.68 | 12.88 | 0.460 | 0.507 | 6 |
| Е | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |

| SYMBOL | MILLIN | IETERS | INC | INCHES | |
|----------|--------|--------|------------|--------|-------|
| STIVIBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| E2 | - | 0.76 | - | 0.030 | 7 |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6, 7 |
| L | 13.52 | 14.02 | 0.532 | 0.552 | |
| L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| L3 | 1.78 | 2.13 | 0.070 | 0.084 | |
| L4 | 0.76 | 1.27 | 0.030 | 0.050 | 2 |
| ØΡ | 3.54 | 3.73 | 0.139 | 0.147 | |
| Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| θ | 90° t | o 93° | 90° to 93° | | |
| | | | | | |

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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